

600V 58mohm Super-Junction Power MOSFET
AK3S60N580TMF

Description:

This SJ device provides good FOM performance, better EMI for customer application.

Features:

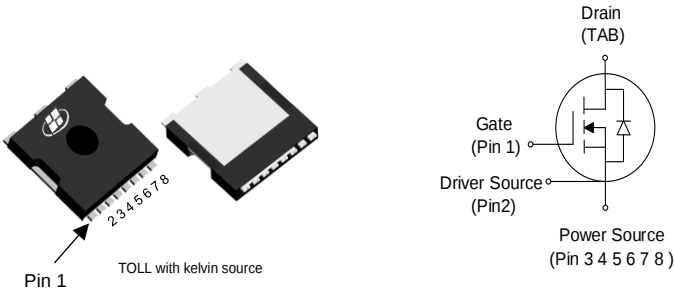
- EMI-Friendly
- RoHS compliant
- Halogen-free
- Wettable Flank for Improved Optical Inspection

Applications:

- High Frequency Switching
- High Efficiency SMPS

Key Performance Parameters:

Parameter	Value	Unit
V_{DS}	600	V
$R_{DS(on), max} @V_{GS} = 10\text{ V}$	58	mΩ
I_D	50	A



Ordering Information:

Ordering Code	Package Type	Marking Code	Form	Packing
AK3S60N580TMF	TOLL	3S60N580TMF	Tape Reel	See the detail package information

Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DS}	Drain - Source Voltage	600	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) ^(Note 1)	50	A
	Drain Current - Continuous ($T_C = 100^\circ\text{C}$)	31	A
I_{DM}	Drain Current - Pulsed ^(Note 2)	150	A
V_{GS}	Gate - Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy ^(Note 3)	540	mJ
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	271	W
dV/dT	MOSFET dv/dt ruggedness, $V_{DS} = 0 \dots 400 \text{ V}$	120	V/ns
	Reverse diode dv/dt, $V_{DS} = 0 \dots 400 \text{ V}$	70	V/ns
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction - to - Case, Steady State	0.46	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction - to - Ambient, Steady State ^(Note 4)	45	$^\circ\text{C/W}$

Notes:

1. The max drain current rating limited by maximum junction temperature
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. $L = 10.8 \text{ mH}$, $V_{DD} = 100 \text{ V}$, $I_{AS} = 10 \text{ A}$, $R_G = 50 \Omega$, Starting $T_J = 25^\circ\text{C}$
4. Mount on minimum PCB layout

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
V _{(BR)DSS}	Drain - Source Breakdown Voltage	V _{GS} = 0 V, I _D = 1 mA	600			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V			10	μA
I _{GSS}	Gate Leakage Current	V _{GS} = ± 30 V, V _{DS} = 0 V			±100	nA
V _{GS(th)}	Gate Threshold voltage	V _{DS} = V _{GS} , I _D = 1 mA	3	3.8	5	V
R _{DS(ON)}	Drain - Source on - state resistance	V _{GS} = 10 V, I _D = 16 A		45	58	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 400 V, V _{GS} = 0 V, f = 1 MHz		2890		pF
C _{oss}	Output Capacitance			63		pF
C _{rss}	Reverse Transfer Capacitance			15		pF
C _{o(er)}	Effective output capacitance, energy related	V _{DS} = 0...400 V, V _{GS} = 0 V		129		pF
C _{o(tr)}	Effective output capacitance, time related	V _{DS} = 0...400 V, V _{GS} = 0 V, I _D =constant		990		pF
R _g	Gate Resistance	f = 1 MHz		6		Ω
Switching Characteristics						
t _{d(on)}	Turn On Delay Time	V _{DD} = 400 V , I _D = 16 A, V _{GS} = 13 V, R _G = 3 Ω		101		ns
t _r	Rise Time			9		ns
t _{d(off)}	Turn Off Delay Time			119		ns
t _f	Fall Time			9		ns
Q _g	Total Gate Charge	V _{DD} = 400 V , I _D = 16 A, V _{GS} = 10 V		95		nC
Q _{gs}	Gate - Source Charge			16		nC
Q _{gd}	Gate - Drain Charge			50		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Body - Diode Forward Current				50	A
I _{SM}	Maximum Pulsed Body - Diode Forward Current				150	A
V _{SD}	Diode Forward Voltage	V _{GS} = 0 V, I _S = 16 A		0.95		V
t _{rr}	Reverse recovery time	V _{DD} = 400 V, I _D = 16 A, di/dt = 100 A/μs		103		ns
Q _{rr}	Reverse recovery charge			0.95		μC
I _{rrm}	Peak Reverse Recovery Current			18		A

Electrical Characteristics Diagrams

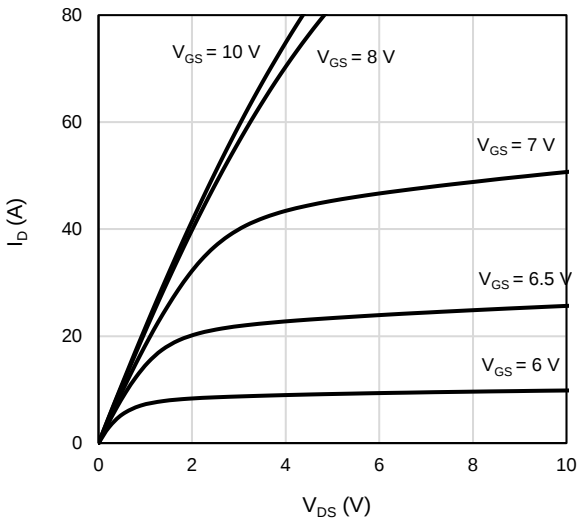


Figure 1: On-Region Characteristics

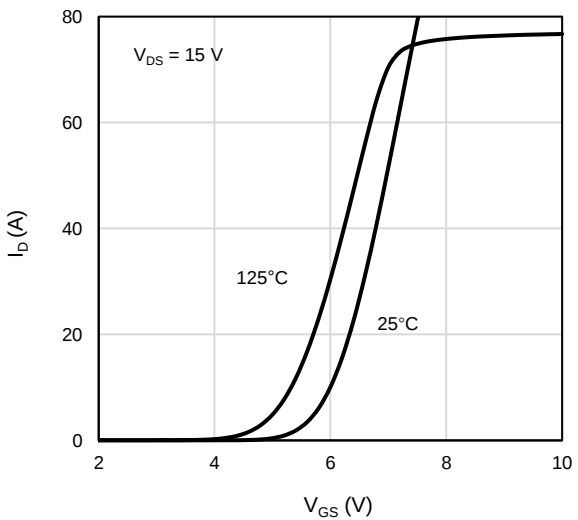


Figure 2: Transfer Characteristics

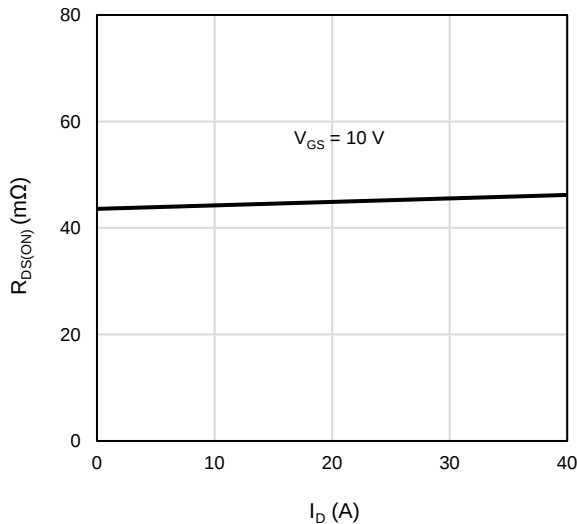


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

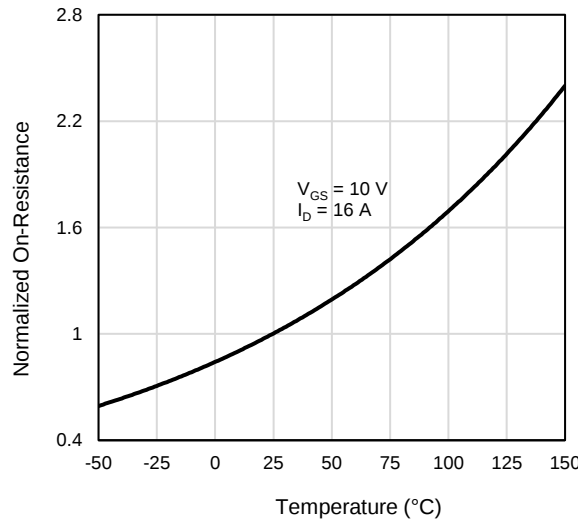


Figure 4: On-Resistance vs. Junction Temperature

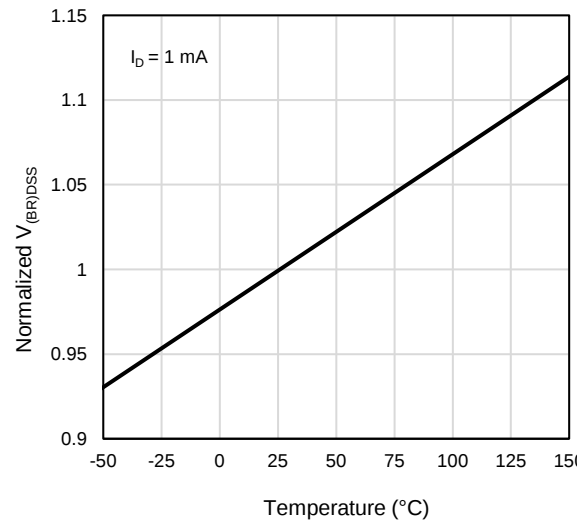


Figure 5: Breakdown Voltage vs. Junction Temperature

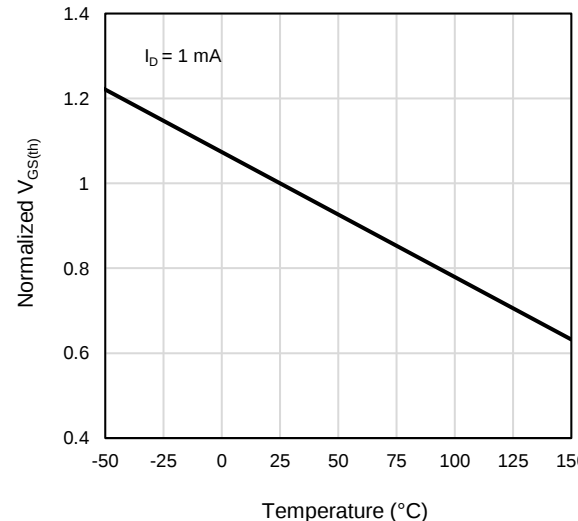


Figure 6: Threshold Voltage vs. Junction Temperature

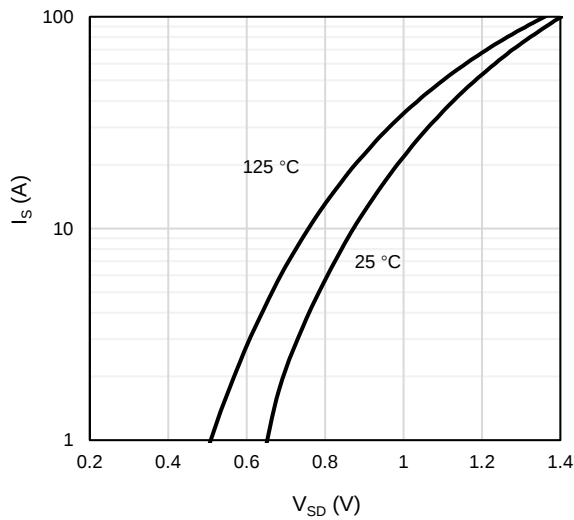


Figure 7: Body-Diode Characteristics

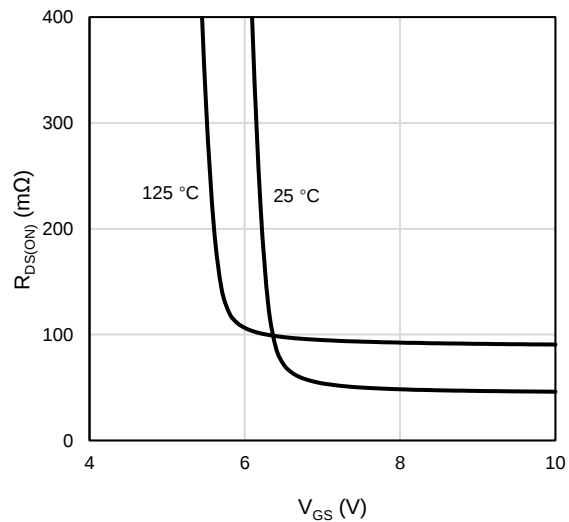


Figure 8: On-Resistance vs. Gate-Source Voltage

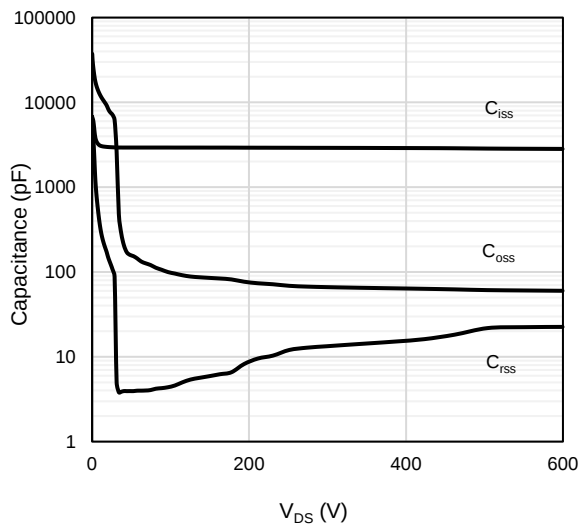


Figure 9: Capacitance Characteristics

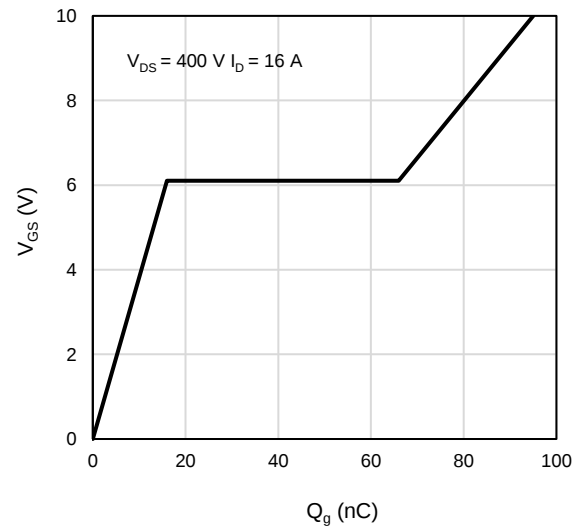


Figure 10: Gate-Charge Characteristics

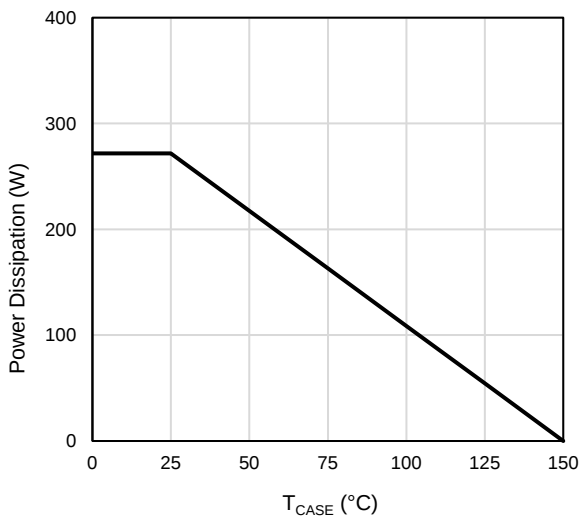


Figure 11: Power De-rating

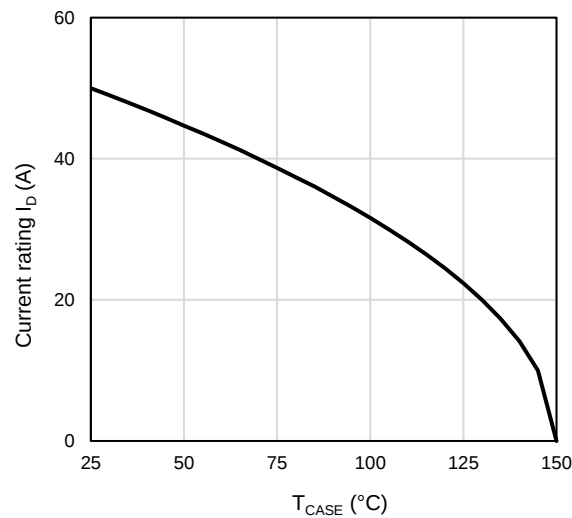


Figure 12: Current De-rating

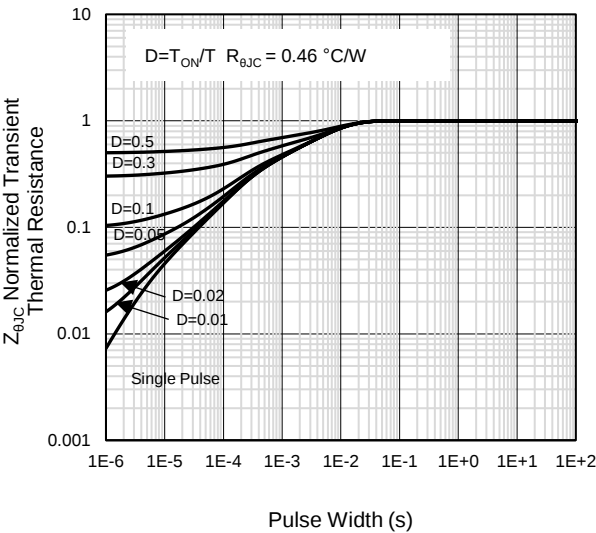


Figure 13: Normalized Maximum Transient Thermal Impedance

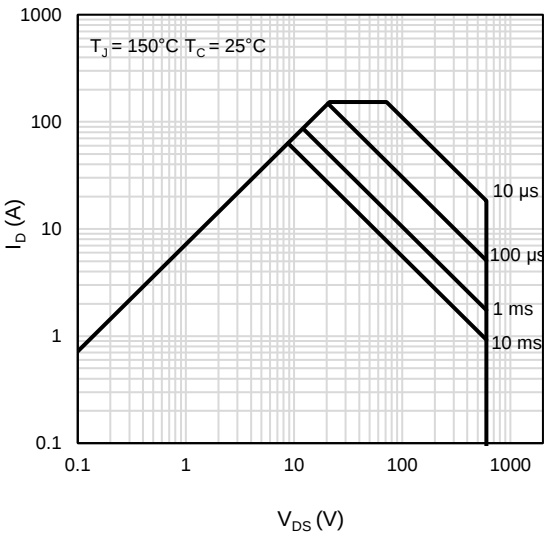
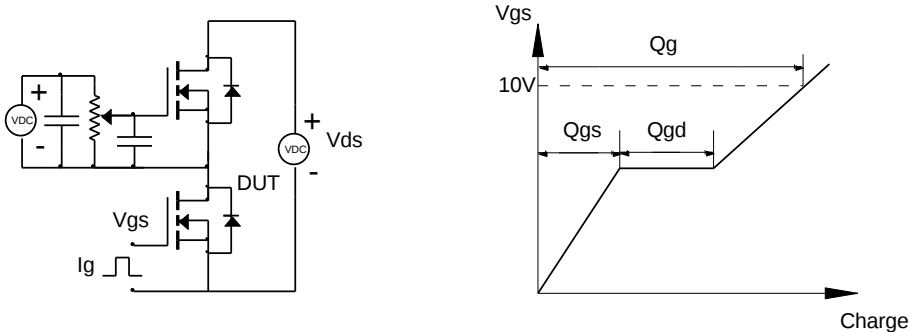


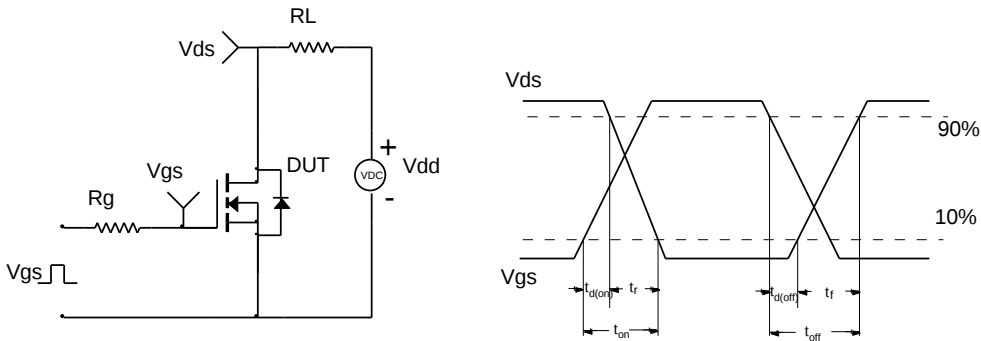
Figure 14: Maximum Forward Biased Safe Operating Area

Test Circuit and Waveform

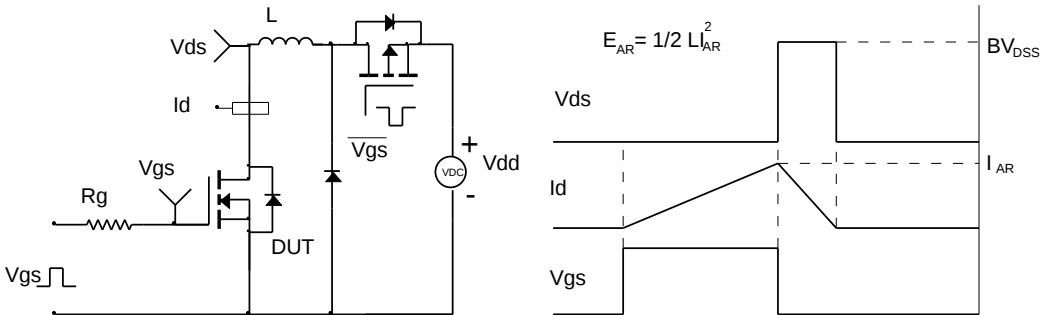
Gate Charge Test Circuit & Waveform



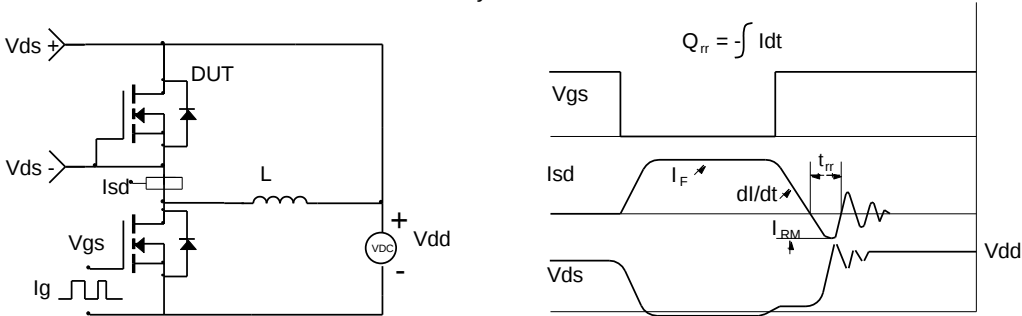
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Revision History

Revision	Released	Remark
Rev.1.0	2025	Initial Release

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Alkaidsemi assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which requires high reliability. Customers using or selling these products for use in medical, life-saving, or life-sustaining applications do so at their own risk and agree to fully indemnify.

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